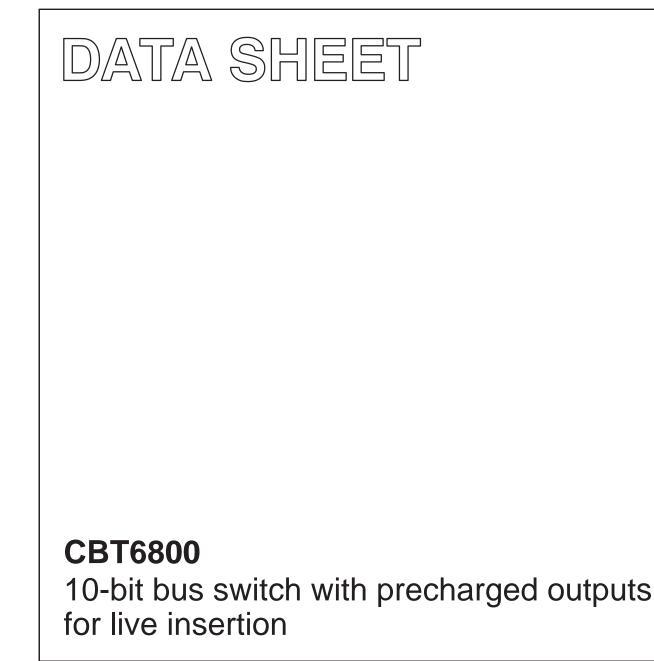
INTEGRATED CIRCUITS



Product specification Supersedes data of 1999 Mar 18 1999 Oct 28



Philips Semiconductors

CBT6800

FEATURES

- 5 Ω switch connection between two ports
- TTL compatible input and output levels
- Outputs are precharged by bias voltage to minimize signal distortion during live insertion
- Latch-up protection exceeds 100 mA per JESD78
- ESD protection exceeds 2000 V HBM per JESD22-A114, 200 V MM per JESD22-A115 and 1000 V CDM per JESD22-C101

DESCRIPTION

The CBT6800 provides ten bits of high-speed TTL-compatible bus switching. The low on-state resistance of the switch allows bi-directional connections to be made while adding near-zero propagation delay. The device also precharges the B port to a user-selectable bias voltage (BIASV) to minimize live-insertion noise.

The CBT6800 is organized as one 10-bit switch with a single enable (\overline{ON}) input. When \overline{ON} is low, the switch is on and port A is connected to port B. When \overline{ON} is high, the switch between port A and port B is open and the B port is precharged to BIASV through the equivalent of a 10 k Ω resistor.

The CBT6800 is characterized for operation from -40°C to 85°C.

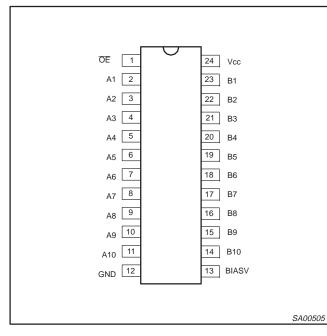
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS T _{amb} = 25°C; GND = 0 V	TYPICAL	UNIT
t _{PLH} t _{PHL}	Propagation delay An to Bn or Bn to An	C _L = 50 pF; V _{CC} = 5 V	250	ps
C _{IN}	Input capacitance – control pin	$V_I = 0 V \text{ or } V_{CC}$	3.5	pF
C _{OUT}	Output capacitance – I/O pins	Outputs disabled; $V_O = 0 V \text{ or } V_{CC}$	8.2	pF
I _{CCZ}	Total supply current	Outputs disabled; V_{CC} =5.5 V	1	μΑ

ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	ORDER CODE	DWG NUMBER
24-Pin Plastic TSSOP Type I	-40°C to +85°C	CBT6800 PW DH	SOT355-1

PIN CONFIGURATION

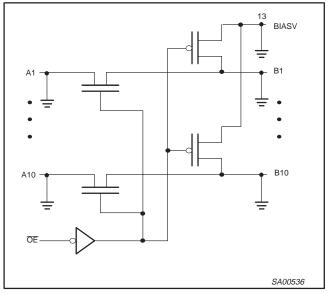


PIN DESCRIPTION

PIN NUMBER	SYMBOL	NAME AND FUNCTION
1	ŌĒ	Output enable
13	BIASV	Precharge bias voltage input
2, 3, 4, 5, 6, 7, 8, 9, 10, 11	A1–A10	A-port I/O pins
23, 22, 21, 20, 19, 18, 17, 16, 15, 14	B1–B10	B-port I/O pins – with active pullup
12	GND	Ground (V)
24	V _{CC}	Positive supply voltage

CBT6800

LOGIC SYMBOL



FUNCTION TABLE

ŌĒ	B1 – B10	FUNCTION		
L	A1 – A10	Connect		
Н	BIASV	Precharge		

H = High voltage level

L = Low voltage level Z = High impedance "off" state

ABSOLUTE MAXIMUM RATINGS^{1, 2}

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +7.0	V
I _{IK}	DC input diode current		-50	mA
VI	DC input voltage ³		-1.2 to +7.0	V
I _{SW}	DC clamp diode current	V _O < 0	-50	mA
T _{stg}	Storage temperature range		-65 to 150	°C
BiasV	DC voltage range		-0.5 to 6.0	V

NOTES:

 Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

 The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.

3. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIM	UNIT	
STWBUL	PARAMETER	Min	Max	UNIT
V _{CC}	DC supply voltage	4.5	5.5	V
BIASV	DC supply voltage	1.3	V _{CC}	V
V _{IH}	High-level input voltage	2.0		V
V _{IL}	Low-level Input voltage		0.8	V
T _{amb}	Operating free-air temperature range	-40	+85	°C

Product specification

CBT6800

DC ELECTRICAL CHARACTERISTICS

				LIMITS		
SYMBOL	PARAMETER	TEST CONDITIONS	T _{amb} =	-40°C to	• +85°C	UNIT
			Min	Typ ¹	Max	
V _{IK}	Input clamp voltage	$V_{CC} = 4.5 \text{ V}; \text{ I}_{\text{I}} = -18 \text{ mA}$			-1.2	V
l _l	Input leakage current – OE	V _{CC} = 5.5 V; V _I = GND or 5.5 V			±5	μΑ
Ι _Ο	Output bias current	$V_{CC} = 4.5 \text{ V}; \text{ BiasV} = 2.4 \text{ V}; V_{O} = 0$	0.25			mA
I _{CC}	Quiescent supply current	$V_{CC} = 5.5 \text{ V}; I_O = 0, V_I = V_{CC} \text{ or GND}$			50	μΑ
ΔI_{CC}	Control pins ²	V_{CC} = 5.5 V, one input at 3.4 V, other inputs at V_{CC} or GND			2.5	mA
CI	Control pins	V _I = 3 V or 0		3.5		pF
C _{O(OFF)}	Off-state capacitance – I/O pins	$V_0 = 3 V \text{ or } 0$; switch off		8.2		pF
		V _{CC} = 4.5 V; V _I = 0 V; I _I = 64 mA		5	7	
r _{on} ³	On-resistance	V _{CC} = 4.5 V; V _I = 0 V; I _I = 30 mA		5	7	Ω
		$V_{CC} = 4.5 \text{ V}; \text{ V}_{I} = 2.4 \text{ V}; \text{ I}_{I} = 15 \text{ mA}$		10	15]
VP	Pass gate voltage	$V_{IN} = V_{CC} = 5.0 \text{ V}, I_{OUT} = -100 \mu\text{A}$	3.4	3.6	3.9	V

NOTES:

All typical values are at V_{CC} = 5 V, T_{amb} = 25°C
This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND
Measured by the voltage drop between the A and the B terminals at the indicated current through the switch. On–state resistance is determined by the lowest voltage of the two (A or B) terminals.

CBT6800

AC CHARACTERISTICS

GND = 0 V; C_L = 50 pF; t_r = $t_f \le 2.5$ ns

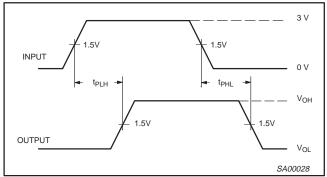
				LIMITS		
SYMBOL	PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = +5.0	0 V ±0.5 V	UNIT
		((000000)	Min	Max	
t _{pd}	Propagation delay ¹	A or B	B or A		.25	ns
t _{PZH} T _{PZL}	BIASV = GND BIASV = 3 V	ŌN	A or B	2.4 3.0	7.7 8.3	ns
t _{PHZ} T _{PLZ}	BIASV = GND BIASV = 3 V	ŌN	A or B	1.0 3.1	5.3 7.8	ns

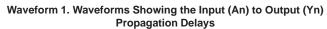
NOTE:

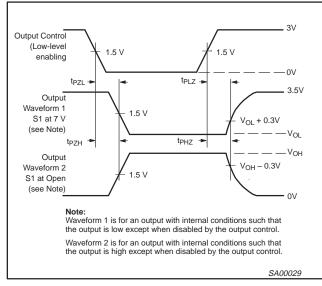
1. This parameter is warranted but not production tested. The propagation delay is based on the RC time constant of the typical on-state resistance of the switch and a load capacitance of 50 pF, when driven by an ideal voltage source (zero output impedance).

AC WAVEFORMS

 V_{M} = 1.5 V, V_{IN} = GND to 3.0 V

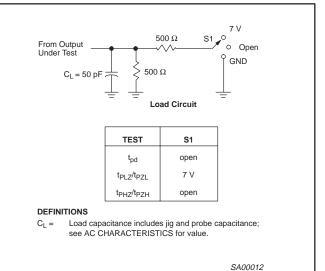






Waveform 2. Waveforms Showing the 3-State Output Enable and Disable Times

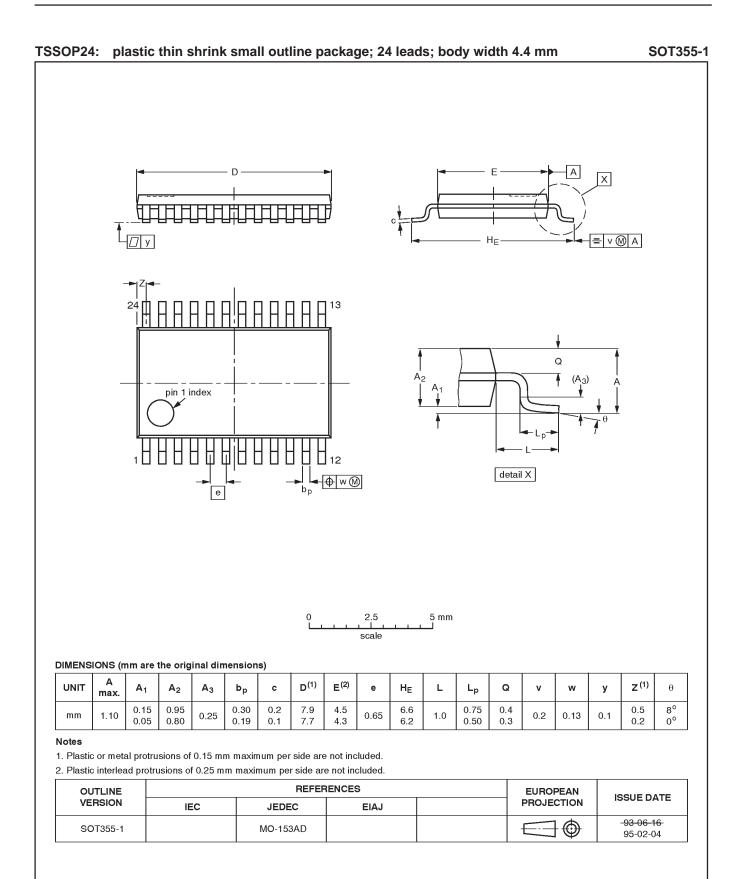
TEST CIRCUIT AND WAVEFORMS



NOTES:

- 1. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 $\Omega,\,t_r$ \leq 2.5 ns, t_f \leq 2.5 ns.
- 2. The outputs are measured one at a time with one transition per measurement.

CBT6800



NOTES

CBT6800

CBT6800

Data sheet status

Data sheet status	Product status	Definition ^[1]
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

[1] Please consult the most recently issued datasheet before initiating or completing a design.

Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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